

Part Number

Customer

Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110} +/- 0.5 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	
	5.0	Secondary Flat Length	none	Wafer Vendor
	6.0	Overall Thickness	363.00 +/- 27.00 μ m	ADE, 100%
	7.0	Total Thickness Variation (TTV)	<10.00um	Granted by process
	8.0	Bow	<70.00um	ADE to ASTM F534, 20%
	9.0	Warp	<70.00um	ADE to ASTM F534, 20%
	10.0	Edge Chips	None	Bright Light, 100%
	11.0	Edge Exclusion	5mm	
HandleSilicon	12.0	Handle Growth Method	CZ	Wafer Vendor
	13.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	14.0	Handle Thickness	350.00 +/- 25.00 μ m	ADE, 100%
	15.0	Handle Doping Type	P	Wafer Vendor
	16.0	Handle Dopant	Boron	Wafer Vendor
	17.0	Handle Resistivity	1 ~ 100 ohm-cm	Wafer Vendor
	18.0	Backside Finish	Polished with oxide and lasermark.	Wafer Vendor
	BuriedOxide	19.0	Oxide Type	Thermal
20.0		Oxide Thickness	10,000.00 +/- 500.00 A	Nanospec centre point, 4%
DeviceSilicon	22.0	Device Growth Method	CZ	Wafer Vendor
	23.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	24.0	Nominal Thickness	12.00 +/- 1.00 μ m	Filmetrics 9 point, 100%
	25.0	Distance to device silicon edge from wafer edge	< 2mm	Granted by process
	26.0	Device Doping Type	P	Wafer Vendor
	27.0	Device Dopant	Boron	Wafer Vendor
	28.0	Device Resistivity	<0.1 ohm-cm	Wafer Vendor
	29.0	Voids	None	Bright Light, 100% (note2)
	30.0	Haze	None	Bright Light, 100% (note2)
	31.0	Scratches	< 5mm total length	Bright Light, 100% (note2)

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Shipping Details	Wafer per box :	Max 25
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information